

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	7583	(oxygen or "o.sub.2") and (inert or nitrogen or "n.sub.2" or helium or he) and plasma	EPO; JPO; DERWENT	ADJ	ON	2009/11/04 08:39
L5	103	L4 and (chamber or reactor or wall or apparatus) with (clean\$4 or etch\$4)	EPO; JPO	ADJ	ON	2009/11/04 08:39
L6	56	carbon and (ar or argon) with (remov\$4 or etch\$4 or sputter\$4 or clean\$4) with (chamber or wall or reactor)	EPO; JPO	ADJ	ON	2009/11/04 08:42
L7	4613	carbon and (ar or argon) with (remov\$4 or etch\$4 or sputter\$4 or clean\$4) with (chamber or wall or reactor)	US-PCPUB; USPAT	ADJ	ON	2009/11/04 08:42
L8	162	l7 and "134"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 08:43
L9	147	l7 and "134"/\$.ccls. and plasma	US-PCPUB; USPAT	ADJ	ON	2009/11/04 08:43
L10	2137	carbon and (ar or argon) with (remov\$4 or etch\$4 or sputter\$4 or clean\$4) with (chamber or wall or reactor) same (plasma or RF or microwave)	US-PCPUB; USPAT	ADJ	ON	2009/11/04 08:43
L11	102	l10 and "134"/\$.ccls.	US-PCPUB; USPAT	ADJ	ON	2009/11/04 08:43
L12	194	l10 and semiconductor. as.	US-PCPUB; USPAT	ADJ	ON	2009/11/04 08:45
L13	114	(without or needed or necessary) with (F or halogen or halide or fluorine) same (cleaning gas or chamber clean or chamber walls adj3 (clean\$4 or etch\$4))	US-PCPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/11/04 09:02

L14	6	(fluorine-free or halogen-free or chloride-free) same (cleaning gas or chamber clean or chamber walls adj3 (clean\$4 or etch\$4))	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/11/04 09:07
L15	88	I12 and (carbon or DLC) with (oxygen or "o. sub.2")	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:15
L16	32	(SiF or silicon fluoride or FSG) same plasma with chamber with clean\$4	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:19
L17	78	(SiF or silicon fluoride or FSG) and plasma with chamber with clean\$4 and fluorine with (free or needed or necessary)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:23
L18	65	I17 not I16	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:25
L19	49	I18 and (oxygen or "o. sub.2" or nitrogen or "n. sub.2" or ar or argon) adj3 plasma	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:26
L20	20	I15 and carbon and (ar or argon) with (remov\$4 or etch\$4 or sputter\$4 or clean\$4) adj3 (chamber or wall or reactor) same (plasma or RF or microwave)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:37
L21	87	I10 and semiconductor energy.as.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:38
L22	2	I21 and "134"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:38
L23	11	("5176791").URPN.	USPAT	ADJ	ON	2009/11/04 09:44
L24	2	("6610211").URPN.	USPAT	ADJ	ON	2009/11/04 09:50
L26	15	carbonaceous film and semiconductor energy. as.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:54
L27	2	carbonaceous film and semiconductor energy. as. and "146930"	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:55
L28	219	(hydrogen or "h.sub.2") plasma with (nitrogen or "n.sub.2") plasma	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:58

L29	3	(hydrogen or "h.sub.2") plasma with (nitrogen or "n.sub.2") plasma with effect	US-PGPUB; USPAT	ADJ	ON	2009/11/04 09:58
L30	6	I28 and "134"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:00
L31	10	hydrocarbon with clean \$4 same season\$4 same (chamber or reactor or wall)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:02
L32	7	frankel.in. and TEOS	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:04
L33	3779	season\$4 same (chamber or reactor or wall)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:10
L34	1581	season\$4 with (chamber or reactor or wall)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:10
L35	290	I34 and season\$4.ab.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:11
L36	23	I35 and hydrocarbon	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:11
L37	5	I36 and "427"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:11
L38	26	I35 and "427"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:11
L39	5	I35 and "427"/\$.ccls. and ("CCl.sub."\$ or chlorine or cl)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:13
L40	196	hydrogen with oxygen with nitrogen trifluoride	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:16
L41	146	I40 and carbon	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:16
L42	32	I41 and ("427"/\$.ccls. or "134"/\$.ccls.)	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:16
L43	24	I42 and wall	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:16
L44	20	I40 and semiconductor energy.as.	US-PGPUB; USPAT	ADJ	ON	2009/11/04 10:18
L47	38	cleaning with carbon with equipment.ti.	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/11/04 10:21
S1	2055	134/1.1.ccls. or 134/22.1.ccls.	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 09:51
S2	583	S1 and (fluorine)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 09:52

S3	539	S2 and plasma	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 09:52
S4	125	S3 and (first or second or multiple step or multi-step or two-step or three-step) with chamber adj2 (clean\$4 or treat\$4)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 09:53
S5	0	"6068729".pn. and (hal \$4 or chlor\$4)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:01
S6	246	(fluorine with chlorine) same cleaning gas	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:04
S7	121	(fluorine with chlorine) same cleaning gas and ("sio.sub.2" or silicon dioxide)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:04
S8	13	(fluorine with chlorine) same cleaning gas and ("sio.sub.2" or silicon dioxide) and ("CCl. sub.4" or "C.sub.2Cl. sub.6")	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:11
S9	3	without with (fluorine with chlorine) same cleaning gas and ("sio. sub.2" or silicon dioxide)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:13
S10	4	without with (fluorine with chlorine) same cleaning gas	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:14
S11	1	10/587394	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:15
S12	37	without with (F or halogen or halide) same cleaning gas	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:29
S13	2	"4786352".pn.	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:40
S14	382	"CCl.sub.4" with (remov \$4 or etch\$4) with (silicon or silicon dioxide or "sio.sub.2" or silica)	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:50
S15	4	S14 and "134"/\$.ccls.	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 10:51

S16	27	S4 and fluorine.ab.	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 11:00
S17	98	S4 not S16	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 11:03
S18	2	11/754601	US-PGPUB; USPAT; EPO; DERWENT	ADJ	ON	2009/10/29 11:36
S19	59	("5843239").URPN.	USPAT	ADJ	ON	2009/10/29 22:52
S20	1	"4786352".pn.	USPAT	ADJ	ON	2009/10/30 09:00
S21	1	"6014979".pn.	USPAT	ADJ	ON	2009/10/30 09:01
S22	7856	(cl or chlorine) with aluminum or ALCI	USPAT	ADJ	ON	2009/10/31 06:46
S23	2437	S22 and (CVD or vapor deposition or chamber)	USPAT	ADJ	ON	2009/10/31 06:46
S24	470	S22 same (CVD or vapor deposition or chamber)	USPAT	ADJ	ON	2009/10/31 06:46
S25	150	S22 same (CVD or vapor deposition)	USPAT	ADJ	ON	2009/10/31 06:46
S26	3	S25 and "134"/\$.ccls.	USPAT	ADJ	ON	2009/10/31 06:47
S27	1900	(cl or chlorine) with react \$4 with aluminum	US-PGPUB; USPAT	ADJ	ON	2009/10/31 06:49
S28	380	S27 and (CVD or vapor deposition)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 06:50
S29	52	S28 and (cl or chlorine) with react\$4 with aluminum same (particle or contamination or chamber wall)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 06:50
S30	1	"20020073922"	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:00
S31	1	S29 and (season\$4 or pre-coat\$4 or precoat \$4)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:04
S32	607	("427"/\$.ccls. or "134"/\$. ccls.) and (season\$4 or pre-coat\$4 or precoat \$4) same (TEOS or silane or silicon or oxide)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:05

S33	390	("427"/\$.ccls. or "134"/\$.ccls.) and (season\$4 or pre-coat\$4 or precoat \$4) with (TEOS or silane or silicon or oxide)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:05
S34	75	("427"/\$.ccls. or "134"/\$.ccls.) and (season\$4 or pre-coat\$4 or precoat \$4) with (TEOS or silane or silicon or oxide) same (plasma or RF)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:06
S35	8	(ultima or hdp) and (chamber adj2 clean\$4) same (oxygen or "o. sub.2" adj2 plasma) same (nitrogen or "n. sub.2" adj2 plasma)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:09
S36	695	(FSG or SiF) and (oxygen or "o.sub.2") with plasma and (nitrogen or "n.sub.2") with plasma	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:39
S37	495	(FSG or SiF) and (oxygen or "o.sub.2") with plasma same (nitrogen or "n.sub.2") with plasma	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:39
S38	7	(FSG or SiF) and (oxygen or "o.sub.2") with plasma same (nitrogen or "n.sub.2") with plasma same chamber adj2 clean\$4	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:39
S39	1	(f or fluorine) adj2 dop \$4 adj2 (silicon or silicon oxide) and (oxygen or "o.sub.2") with plasma same (nitrogen or "n.sub.2") with plasma same chamber adj2 clean\$4	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:42
S40	454	(FSG or SiF) and (oxygen or "o.sub.2") with (nitrogen or "n. sub.2") with plasma	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:50
S41	68	S40 and ("134"/\$.ccls. or "427"/\$.ccls.)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:51
S42	150	S40 and chamber with (treat\$4 or pretreat\$4 or clean\$4)	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:53

S43	1073	chamber adj3 clean\$4 and (oxygen or "o. sub.2") with plasma and (nitrogen or "n.sub.2") with plasma	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:55
S44	103	chamber adj3 clean\$4. ab. and (oxygen or "o. sub.2") with plasma and (nitrogen or "n.sub.2") with plasma	US-PGPUB; USPAT	ADJ	ON	2009/10/31 07:56
S45	12	(silicon \$2oxide or "sio. sub.2") same (non-volatile) same (cl or chlorine)	US-PGPUB; USPAT	ADJ	ON	2009/11/02 08:47
S46	86	(silicon \$2oxide or "sio. sub.2") with (cl or chlorine) same (\$4volatile or volatil\$4)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 09:31
S47	3	S46 and "427"/\$.ccls.	US-PGPUB; USPAT	ADJ	ON	2009/11/03 09:32
S48	1	"20070181145" and (electron temperature or eV)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 10:11
S49	7583	(oxygen or "o.sub.2") and (inert or nitrogen or "n.sub.2" or helium or he) and plasma	EPO; JPO; DERWENT	ADJ	ON	2009/11/03 10:49
S50	1284	S49 and (chamber or reactor or wall or apparatus) and (clean\$4 or etch\$4)	EPO; JPO; DERWENT	ADJ	ON	2009/11/03 10:49
S51	142	S49 and (chamber or reactor or wall or apparatus) and (clean\$4 or etch\$4)	EPO; JPO	ADJ	ON	2009/11/03 10:50
S52	482	S50 and (oxygen or "o. sub.2") with plasma and (inert or nitrogen or "n. sub.2" or helium or he) with plasma	EPO; JPO; DERWENT	ADJ	ON	2009/11/03 10:50
S53	448	S52 and (oxygen or "o. sub.2") with plasma same (inert or nitrogen or "n.sub.2" or helium or he) with plasma	EPO; JPO; DERWENT	ADJ	ON	2009/11/03 10:50
S54	96	S51 and (semiconductor or film or deposition or seasoning or electronics)	EPO; JPO	ADJ	ON	2009/11/03 10:51

S56	22	ito.in. and aoyanagi.in. and carbon	EPO; JPO	ADJ	ON	2009/11/03 11:04
S59	24476	(oxygen or "o.sub.2") same (inert or nitrogen or "n.sub.2" or helium or he) same plasma	US-PGPUB; USPAT	ADJ	ON	2009/11/03 11:10
S60	145	S59 and (134/22.1.ccls. or 134/22.18.ccls. or 134/26.ccls. or 134/30,34,37,42.ccls.)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 11:10
S62	20	S60 and (two-step or multi\$3 step)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 11:13
S63	125	S60 not S62	US-PGPUB; USPAT	ADJ	ON	2009/11/03 11:22
S64	873	season\$4 with chamber	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:17
S65	1	"20020073922"	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:18
S66	75	season\$4 with chamber with particle	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:19
S67	1	season\$4 with chamber with particle same (chlorine or Cl)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:25
S68	0	season\$4 with chamber with particle and (chlorine or Cl) with clean\$4 gas	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:32
S69	13	season\$4 with chamber with particle and (chlorine or Cl)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:32
S70	1	bayer.in. and stockhausen.in.	US-PGPUB; USPAT; EPO	ADJ	ON	2009/11/03 12:39
S72	37	ELSCHNER.in. and clean \$4	US-PGPUB; USPAT; EPO	ADJ	ON	2009/11/03 12:45
S73	6478	semiconductor energy. as. and (remov\$4 or etch \$4 or clean\$4) same (carbon or deposit\$4 or film)	US-PGPUB; USPAT; EPO	ADJ	ON	2009/11/03 12:58
S74	3739	semiconductor energy. as. and (remov\$4 or etch \$4 or clean\$4) same (carbon or deposit\$4 or film) same plasma	US-PGPUB; USPAT; EPO	ADJ	ON	2009/11/03 12:59
S75	3735	semiconductor energy. as. and (remov\$4 or etch \$4 or clean\$4) same (carbon or deposit\$4 or film) same plasma	US-PGPUB; USPAT	ADJ	ON	2009/11/03 12:59

S76	1703	semiconductor energy. as. and (remov\$4 or etch \$4 or clean\$4) same (carbon or deposit\$4 or film) same plasma same (nitrid\$6 or oxidiz\$4 or oxidation)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 13:00
S77	8	S76 and ("134"/\$.ccls.)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 13:00
S78	22	S75 and ("134"/\$.ccls.)	US-PGPUB; USPAT	ADJ	ON	2009/11/03 13:07
S79	49	("4816113").URPN.	USPAT	ADJ	ON	2009/11/03 13:10
S80	1	chamber adj3 clean\$4 adj5 remov\$4 adj (o or oxygen or "o.sub.2" or CO)	USPAT	ADJ	ON	2009/11/03 13:14
S81	1	S52 and without (fluorine or F)	EPO; JPO	ADJ	ON	2009/11/03 13:16
S82	2	S52 and without with (fluorine or F)	EPO; JPO	ADJ	ON	2009/11/03 13:17

EAST Search History (Interference)

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11/4/2009 11:41:30 AM**C:\ Documents and Settings\ jmiller5\ My Documents\ EAST\ Workspaces\ 10-587394 - no F
clean gases.wsp**